



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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NTUD3170NZ

Small Signal MOSFET

20 V, 220 mA, Dual N-Channel, 1.0 mm x 1.0 mm SOT-963 Package

Features

- Dual N-Channel MOSFET
- Offers a Low $R_{DS(ON)}$ Solution in the Ultra Small 1.0 x 1.0 mm Package
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics
- This is a Pb-Free Device

Applications

- General Purpose Interfacing Switch
- Optimized for Power Management in Ultra Portable Equipment
- Analog Switch

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	20	V
Gate-to-Source Voltage		V_{GS}	± 8	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	220	mA
		$T_A = 85^\circ\text{C}$	160	
	$t \leq 5 \text{ s}$	$T_A = 25^\circ\text{C}$	280	
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	125	mW
	$t \leq 5 \text{ s}$		200	
Pulsed Drain Current		$t_p = 10 \mu\text{s}$	I_{DM}	800 mA
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode) (Note 2)		I_S	200	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

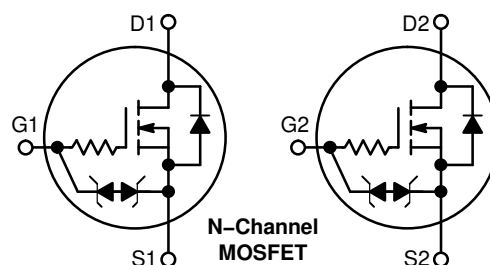
1. Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.
2. Pulse Test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$



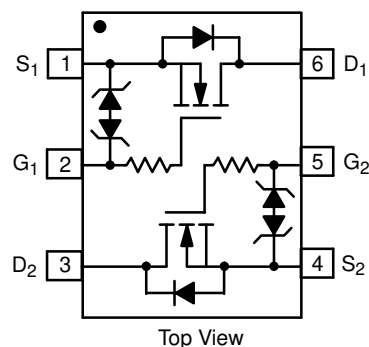
ON Semiconductor®

www.onsemi.com

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D Max
20 V	1.5 Ω @ 4.5 V	0.22 A
	2.0 Ω @ 2.5 V	
	3.0 Ω @ 1.8 V	
	4.5 Ω @ 1.5 V	



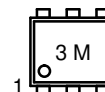
PINOUT: SOT-963



MARKING DIAGRAM



SOT-963
CASE 527AD



3 = Specific Device Code
M = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

NTUD3170NZ

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	1000	°C/W
Junction-to-Ambient – $t = 5$ s (Note 3)		600	

3. Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = 250$ μ A	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0$ V, $V_{DS} = 5$ V	$T_J = 25^\circ\text{C}$		50	nA
			$T_J = 85^\circ\text{C}$		200	nA
		$V_{GS} = 0$ V, $V_{DS} = 16$ V	$T_J = 25^\circ\text{C}$		100	nA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 5.0$ V			± 100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250$ μ A	0.4		1.0	V
Drain-to-Source On Resistance	$R_{DS(ON)}$	$V_{GS} = 4.5$ V, $I_D = 100$ mA		0.75	1.5	Ω
		$V_{GS} = 2.5$ V, $I_D = 50$ mA		1.0	2.0	
		$V_{GS} = 1.8$ V, $I_D = 20$ mA		1.4	3.0	
		$V_{GS} = 1.5$ V, $I_D = 10$ mA		1.8	4.5	
		$V_{GS} = 1.2$ V, $I_D = 1.0$ mA		2.8		
Forward Transconductance	g_{FS}	$V_{DS} = 5.0$ V, $I_D = 125$ mA		0.48		S
Source-Drain Diode Voltage	V_{SD}	$V_{GS} = 0$ V, $I_S = 10$ mA		0.6	1.0	V

CAPACITANCES

Input Capacitance	C_{ISS}	$f = 1.0$ MHz, $V_{GS} = 0$ V $V_{DS} = 15$ V		12.5		pF
Output Capacitance	C_{OSS}			3.6		
Reverse Transfer Capacitance	C_{RSS}			2.6		

SWITCHING CHARACTERISTICS, $V_{GS} = 4.5$ V (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5$ V, $V_{DD} = 10$ V, $I_D = 200$ mA, $R_G = 2.0$ Ω		16.5		ns
Rise Time	t_r			25.5		
Turn-Off Delay Time	$t_{d(OFF)}$			142		
Fall Time	t_f			80		

4. Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

Device	Package	Shipping†
NTUD3170NZT5G	SOT-963 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

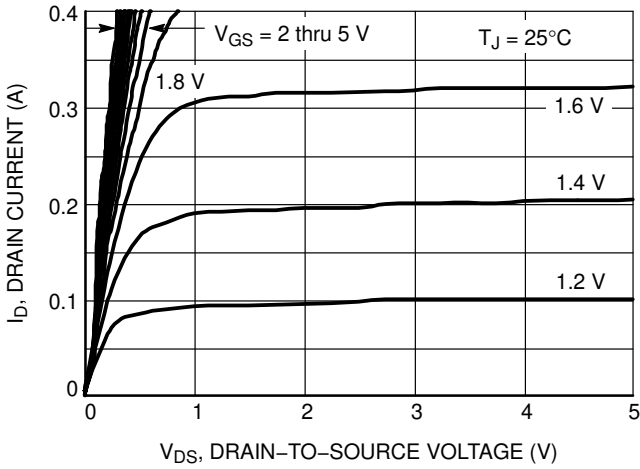


Figure 1. On-Region Characteristics

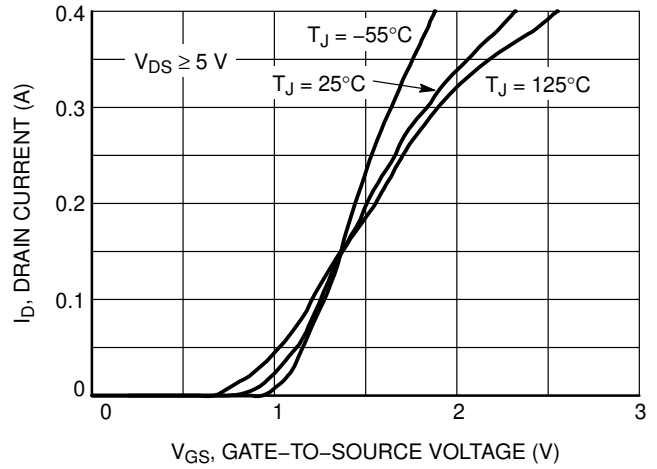


Figure 2. Transfer Characteristics

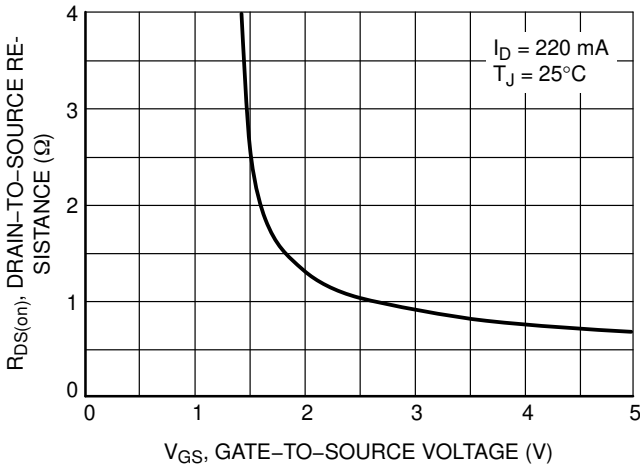


Figure 3. On-Resistance vs. Gate Voltage

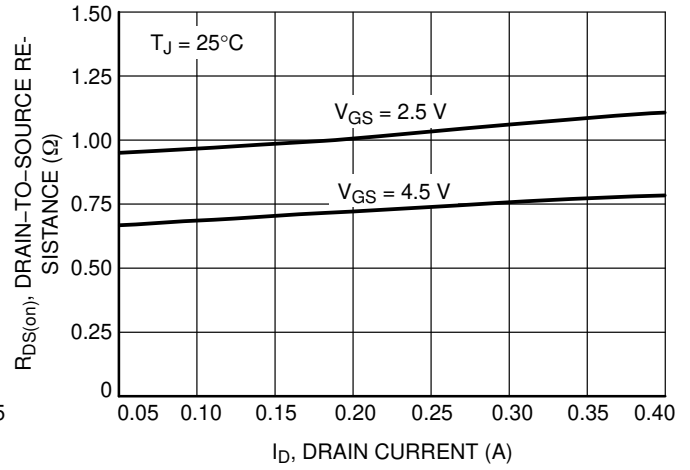


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

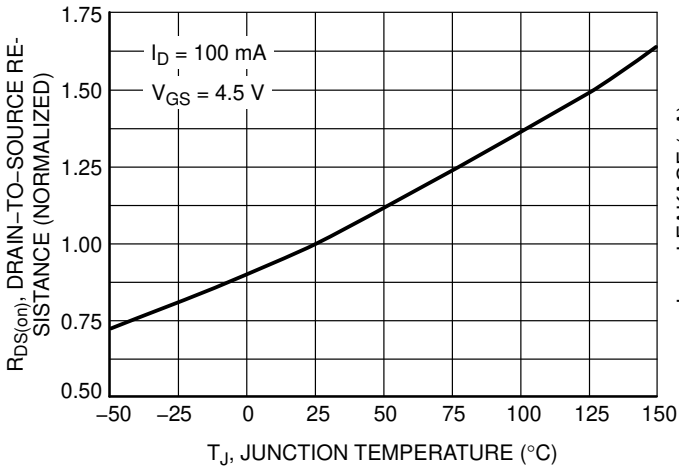


Figure 5. On-Resistance Variation with Temperature

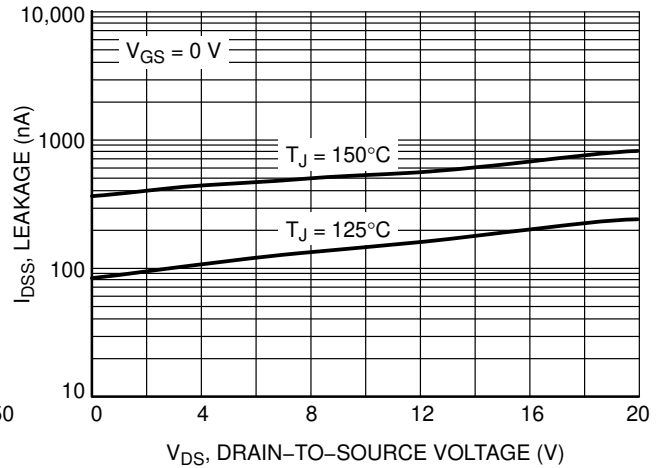


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

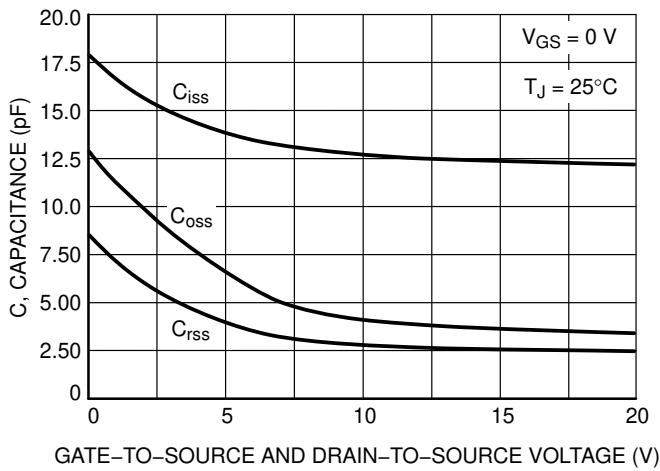


Figure 7. Capacitance Variation

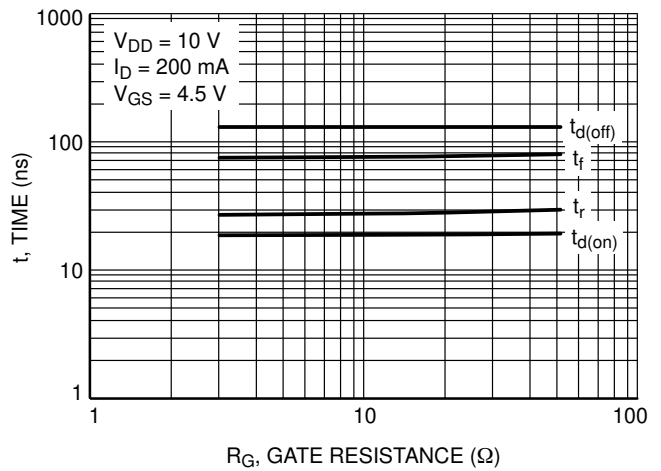


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

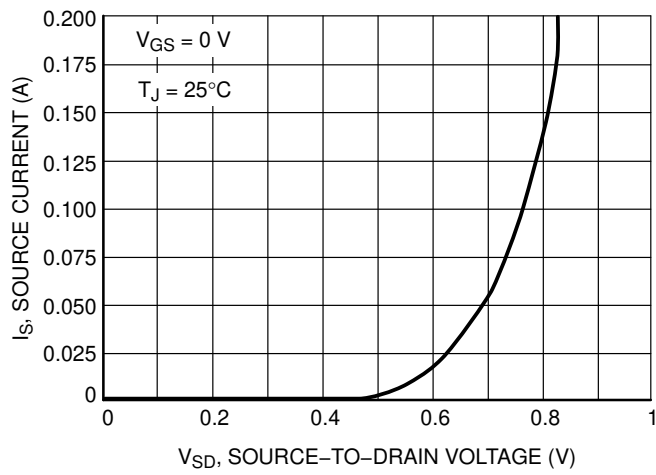
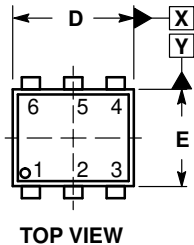


Figure 9. Diode Forward Voltage vs. Current

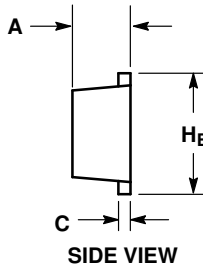
NTUD3170NZ

PACKAGE DIMENSIONS

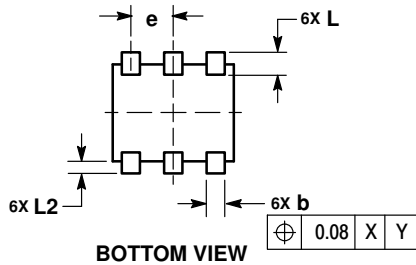
SOT-963
CASE 527AD
ISSUE E



TOP VIEW



SIDE VIEW



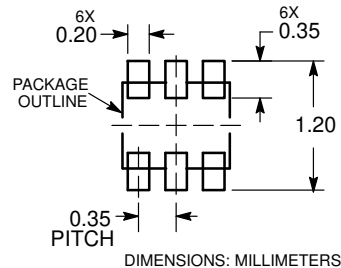
BOTTOM VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.10	0.15	0.20
C	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
HE	0.95	1.00	1.05
L	0.19 REF		
L2	0.05	0.10	0.15

RECOMMENDED MOUNTING FOOTPRINT



DIMENSIONS: MILLIMETERS

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